

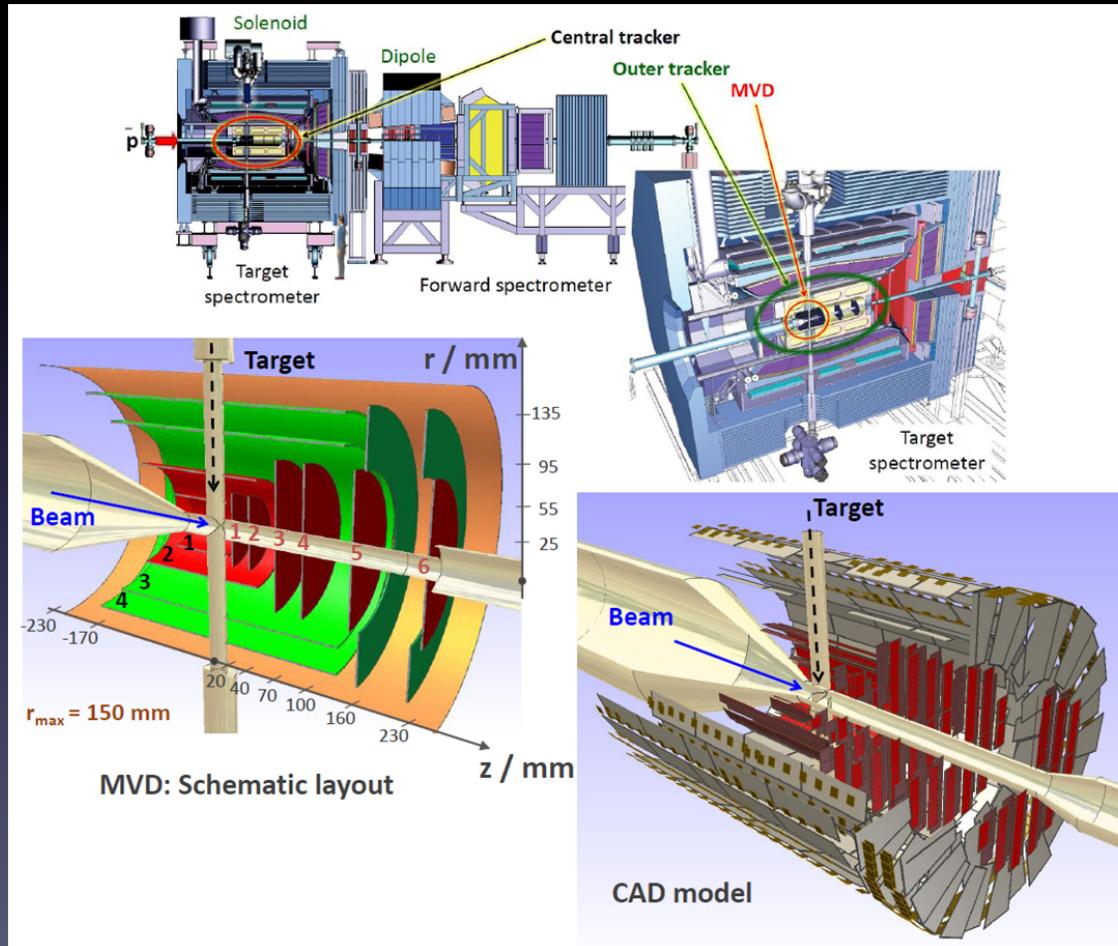
A Low-Power Front-End Amplifier for the Microstrip Sensors of the PANDA Microvertex Detector

Tesi Magistrale

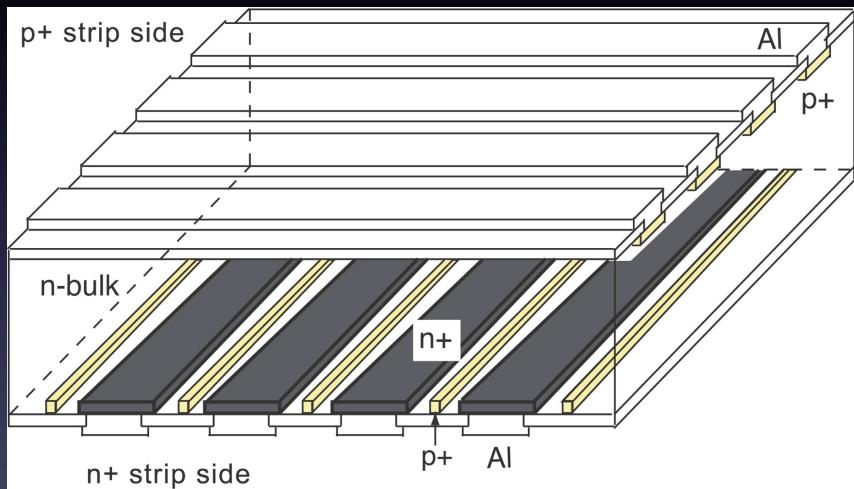
Tesista: Valentino Di Pietro

Relatore: Angelo Rivetti

Microvertex Detector

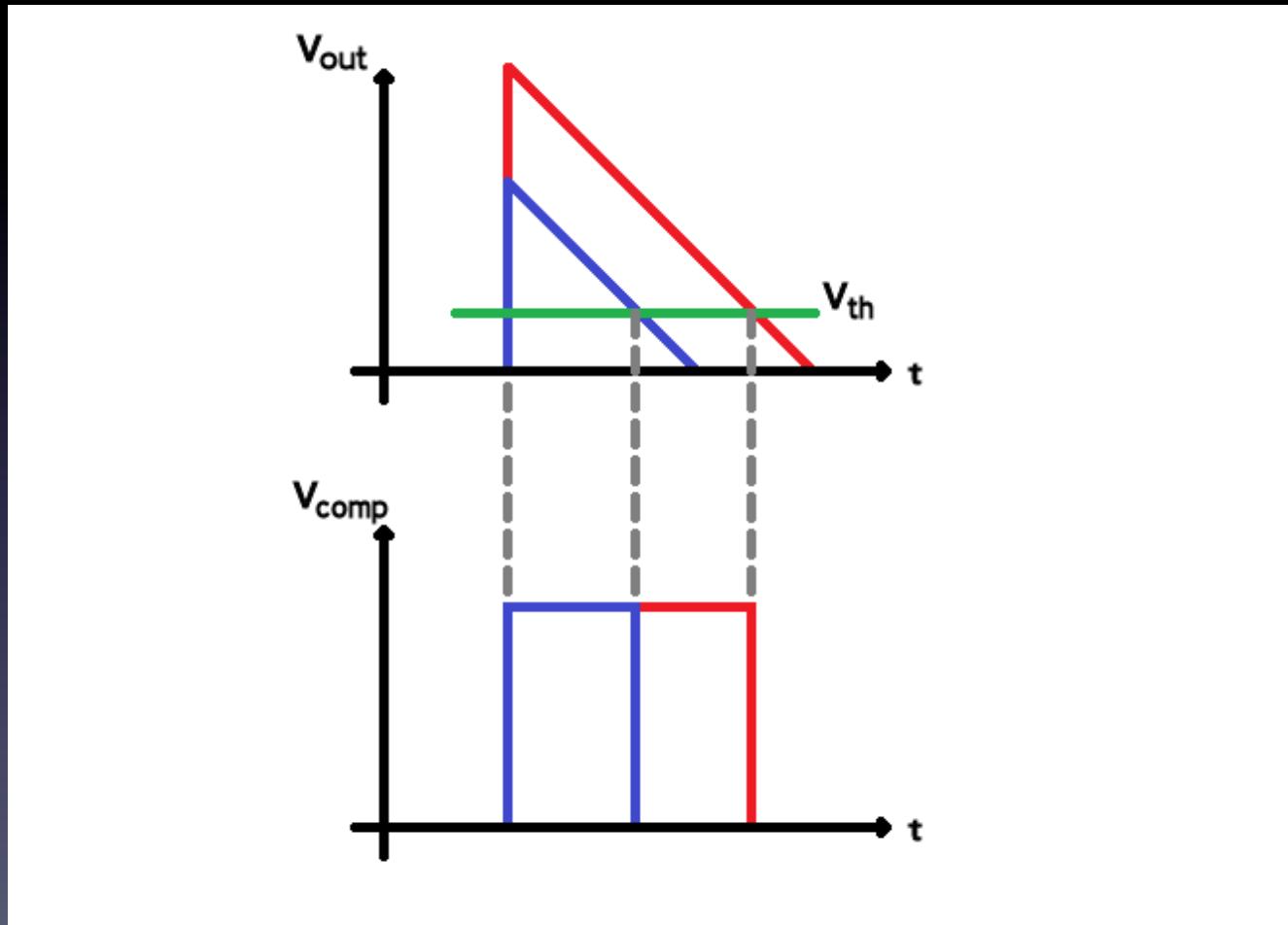


Microstrip Sensors requirements

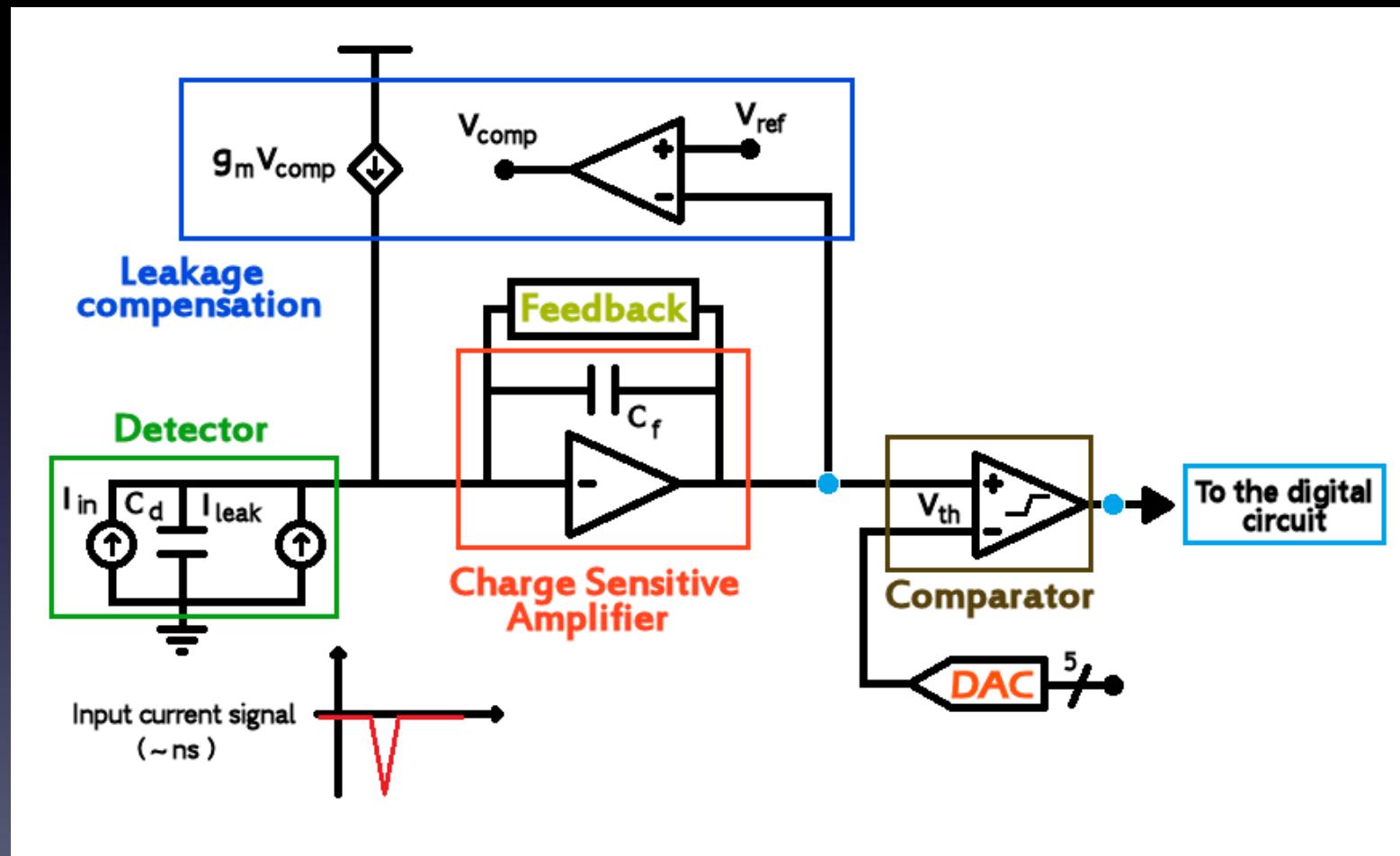


- Specifications
 - Length ~ 8-10 cm
 - Width ~ 60-80 μm
 - Pitch ~ 100 μm
 - $C_{\text{det}} \sim 5\text{-}30 \text{ pF}$
- Goals
 - Dynamic range ~ 9 bits
 - Noise < 2000 e⁻
 - Power consumption $\leq 4 \text{ mW/ch}$

ToT technique



Pixel readout cell

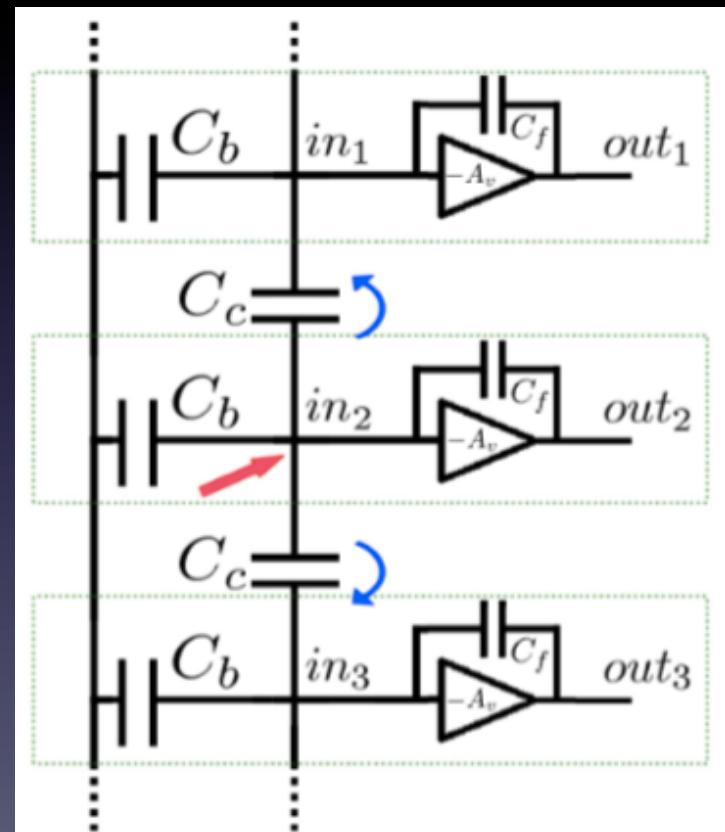


Pixels vs Strips

Speed

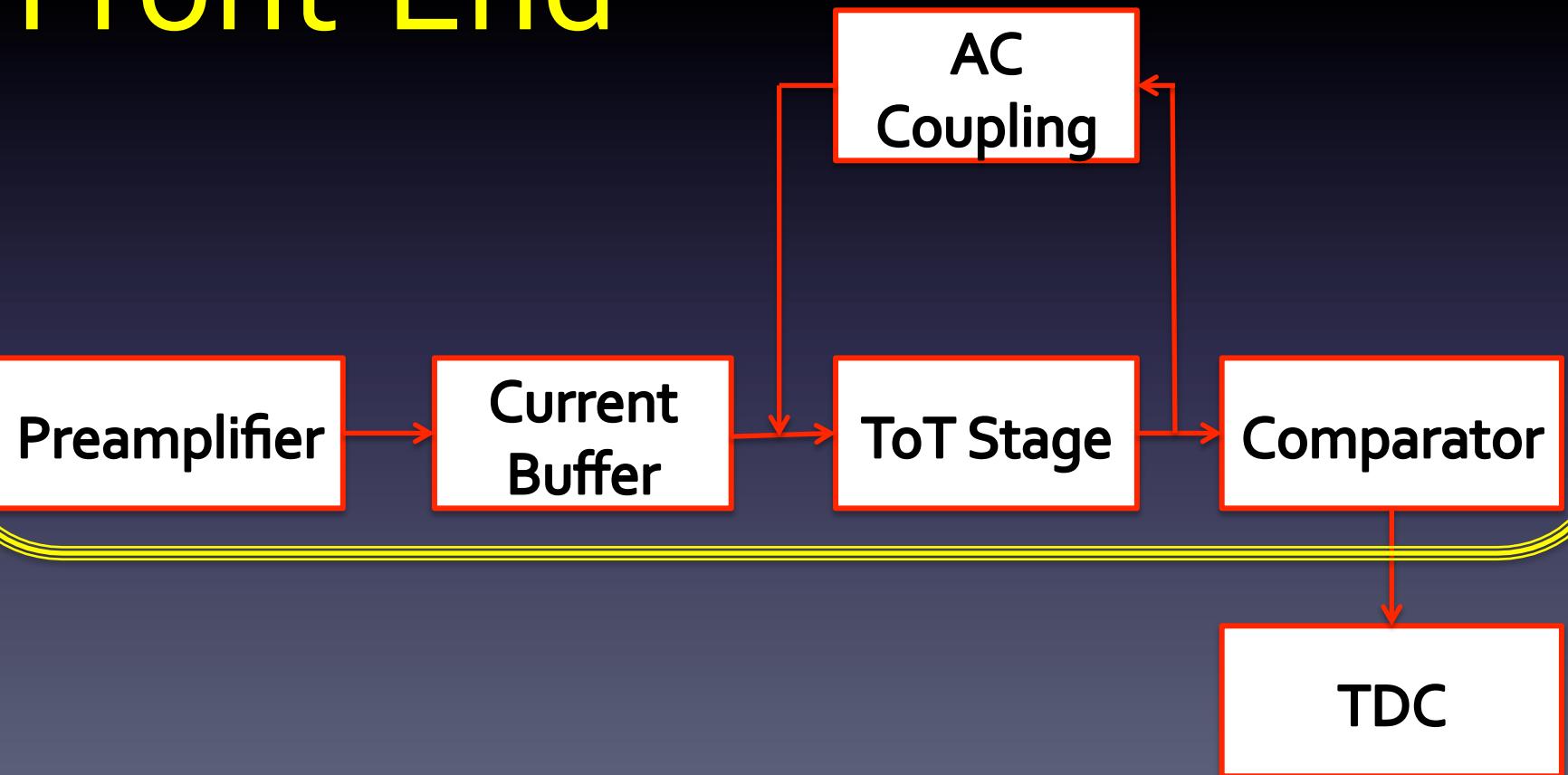
- Pixels event rate ~ 1 kHz
- Strips event rate ~ 30 kHz

Cross-talk

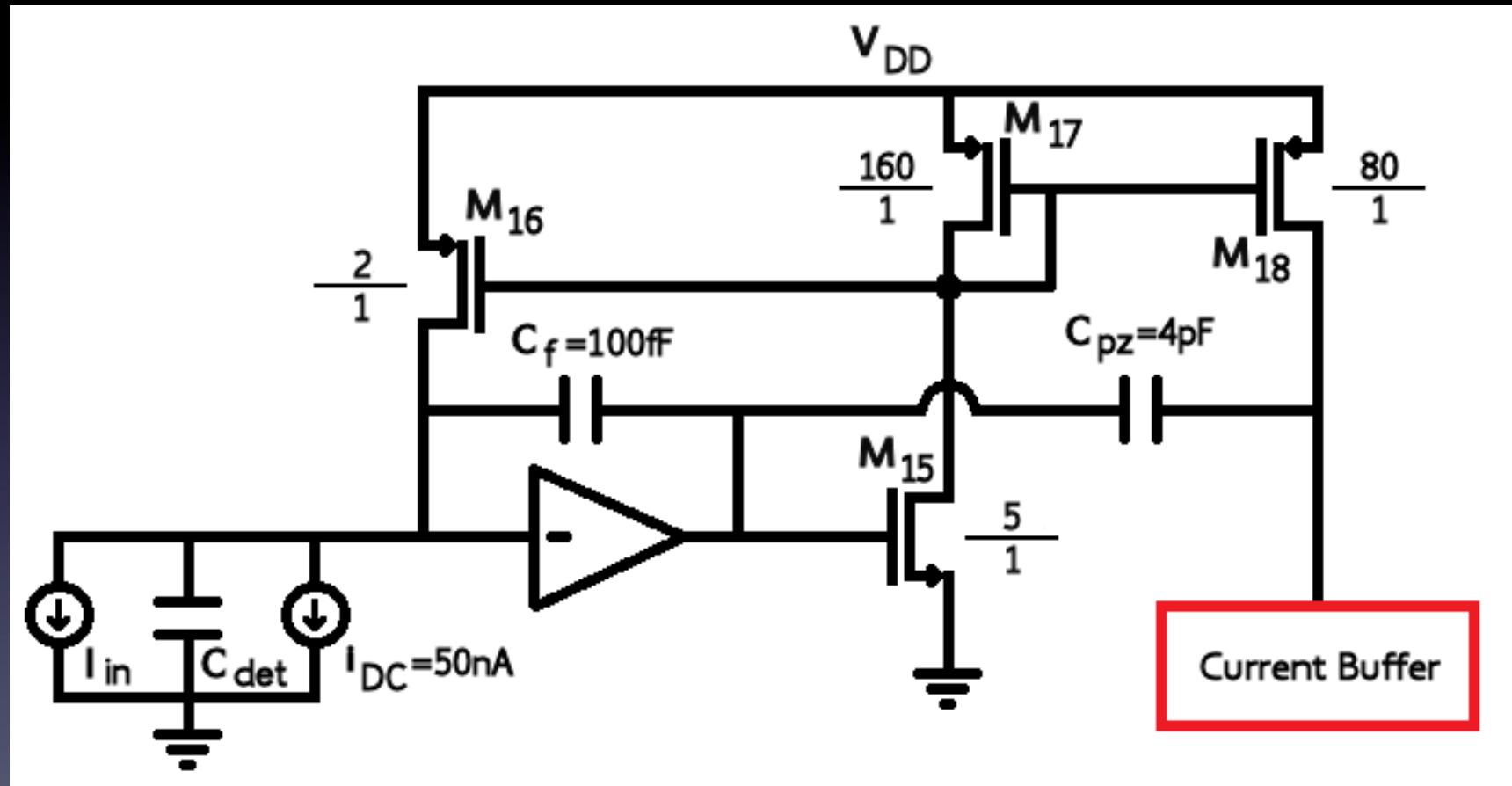


Implemented input stage

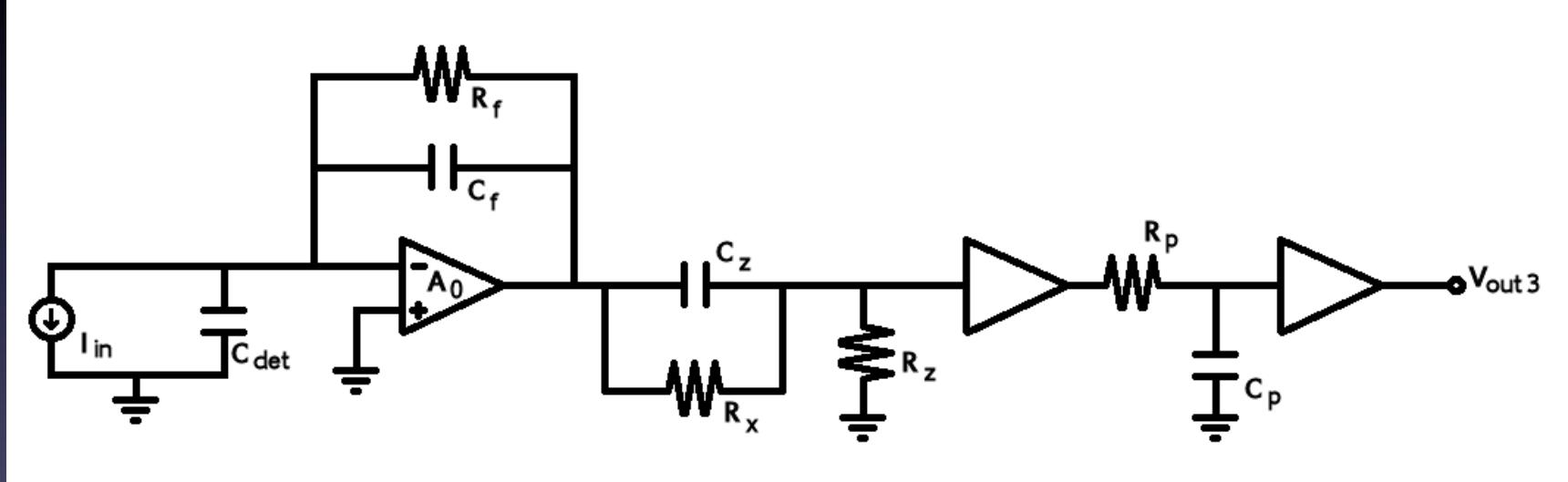
Front-End



Implemented FE Stage: CSA

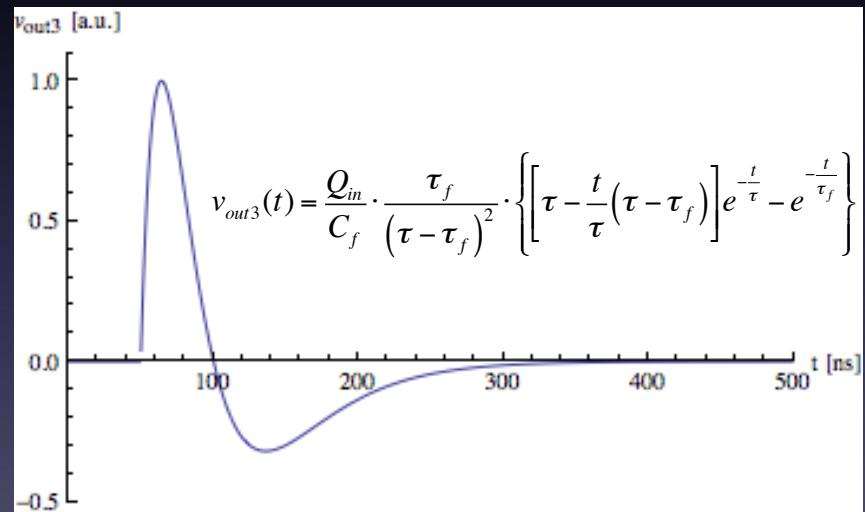


Pole-zero cancellation (1)

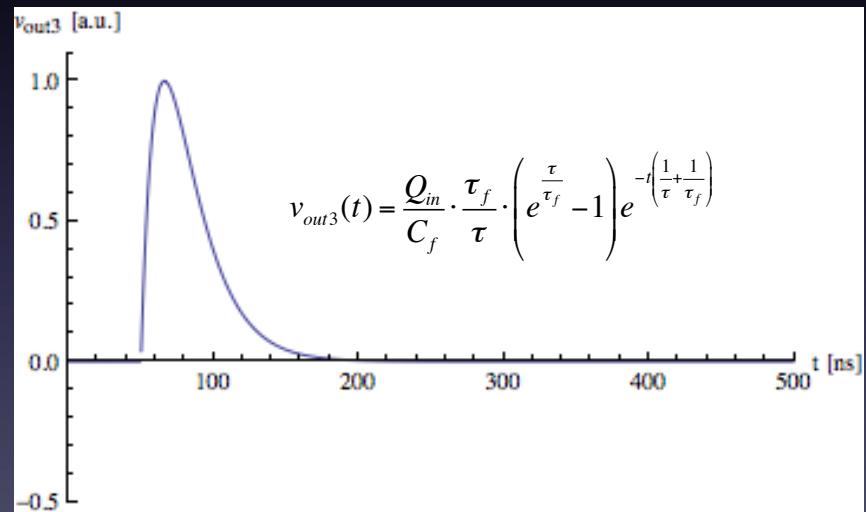


Pole-zero cancellation (2)

Without cancellation



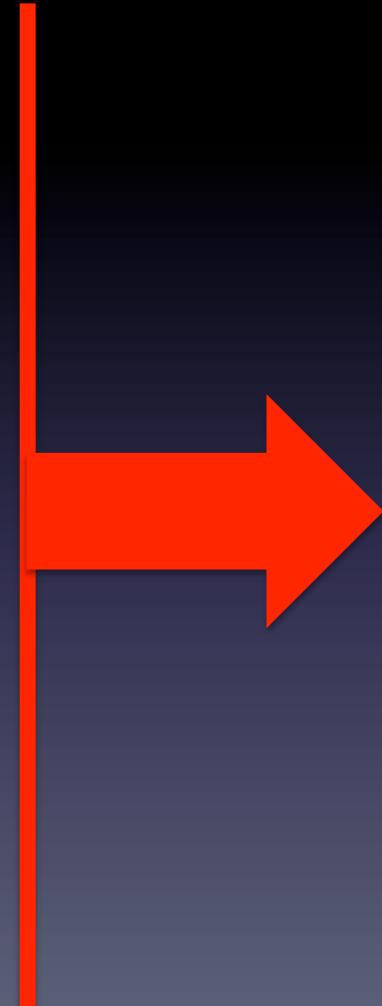
With cancellation



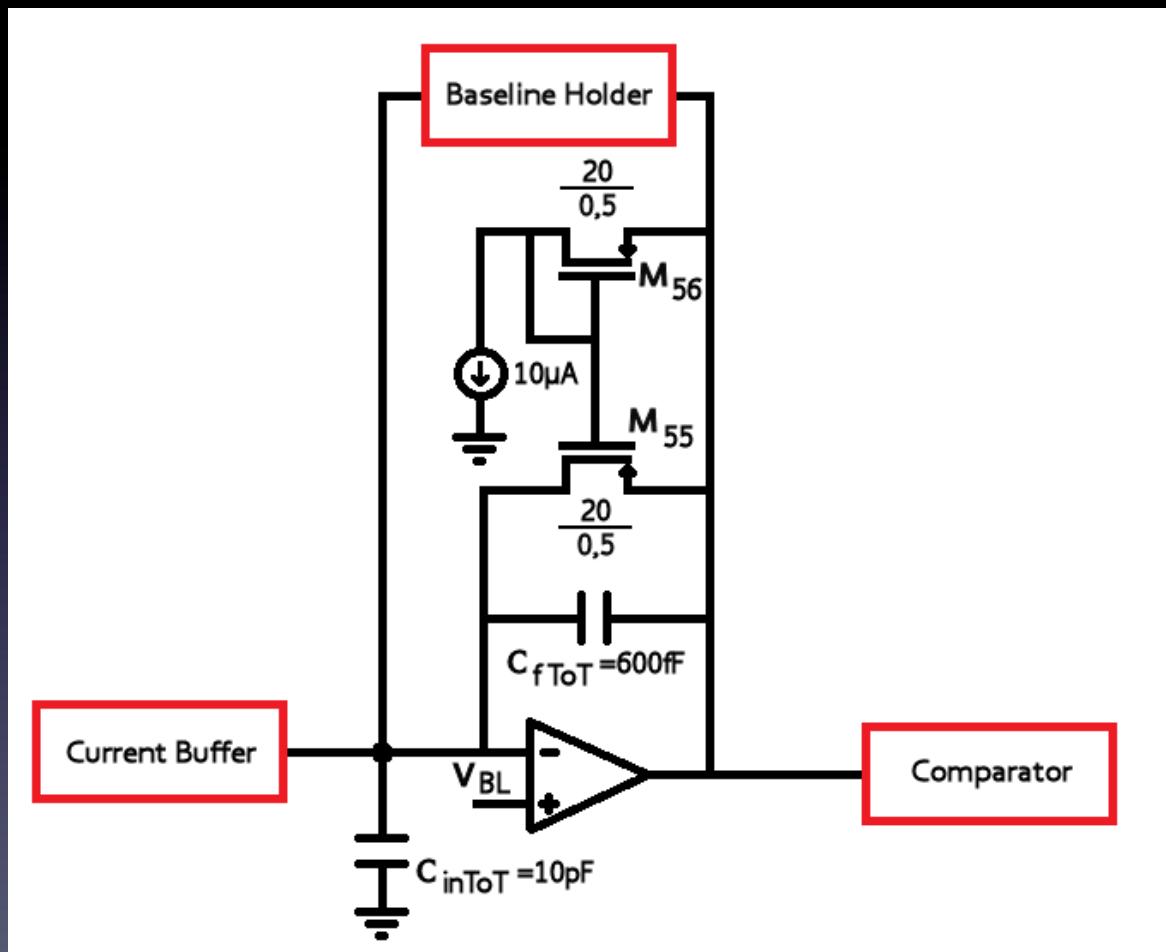
$$H_3(s) = \frac{Q_{in}}{C_f} \cdot \frac{\tau_f}{1+s\tau_f} \cdot \frac{s\tau}{1+s\tau} \cdot \frac{1}{1+s\tau}$$

$$H_3(s) = \frac{Q_{in}}{C_f} \cdot \frac{\tau}{1+s\tau \left(1 + \frac{1}{s\tau_f} \right)} \cdot \frac{1}{1+s\tau}$$

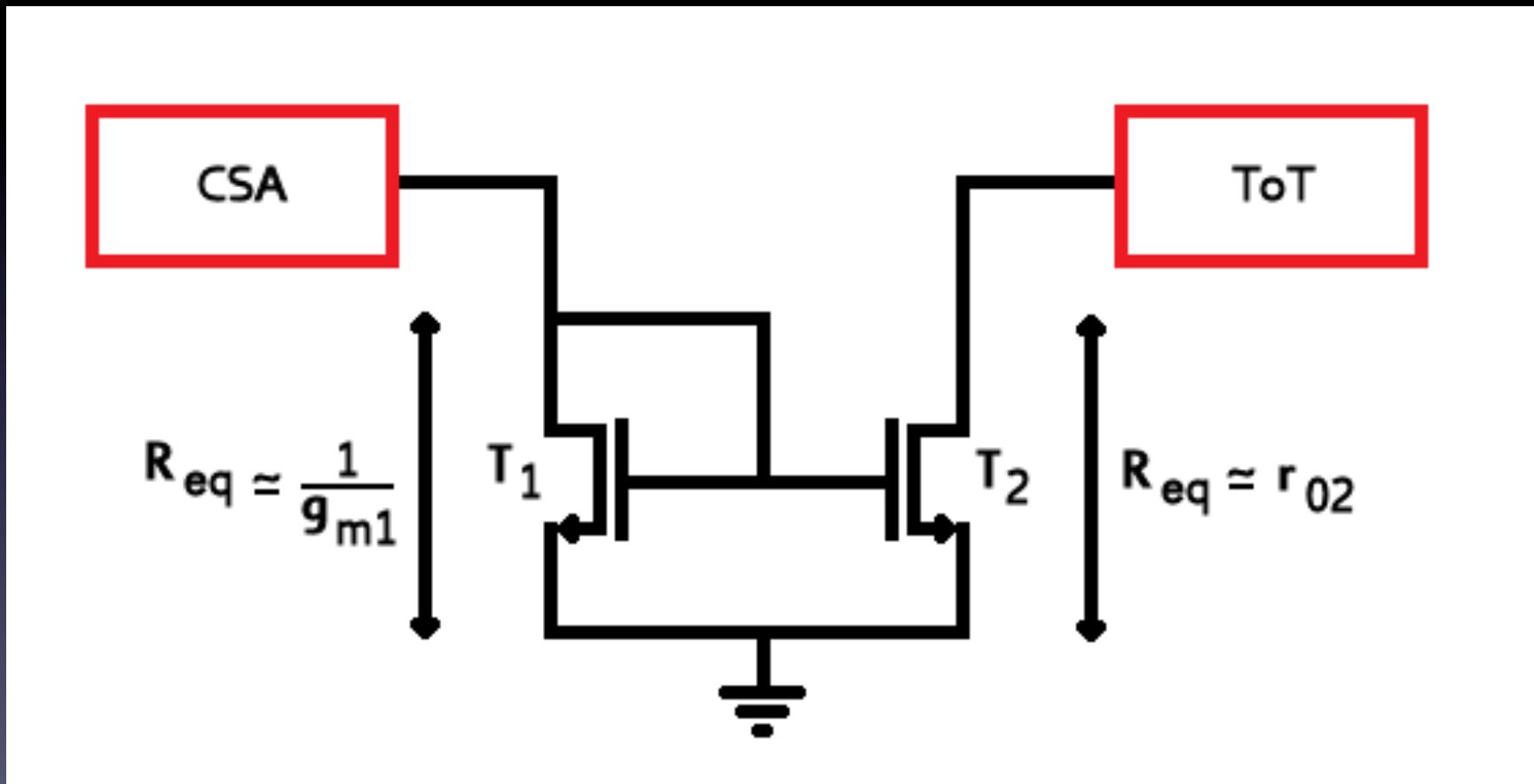
Implemented pole-zero cancellation

- $(R_f)_{eq} = \frac{v_{preamp}}{I_f} = \left(\frac{g_{m17}}{g_{m16}} \right) \cdot \frac{1}{g_{m15}}$
 - $(R_x)_{eq} = \frac{v_{out}}{I_{out}} = \left(\frac{g_{m17}}{g_{m18}} \right) \cdot \frac{1}{g_{m15}}$
 - $\frac{g_{m17}}{g_{m16}} = 80$
 - $\frac{g_{m17}}{g_{m18}} = 2$
- 
- $$\frac{(R_f)_{eq}}{(R_x)_{eq}} = \frac{C_{pz}}{C_f} = 40$$

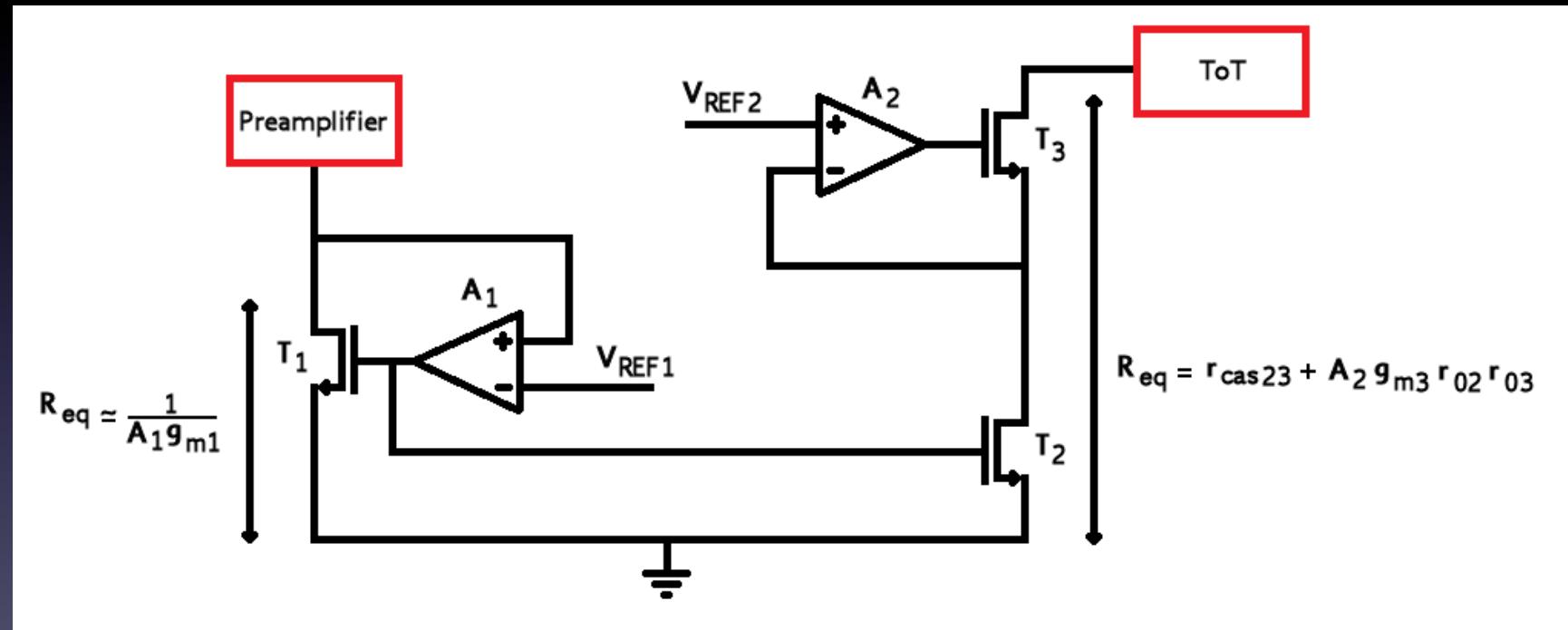
Implemented FE stage: ToT Stage



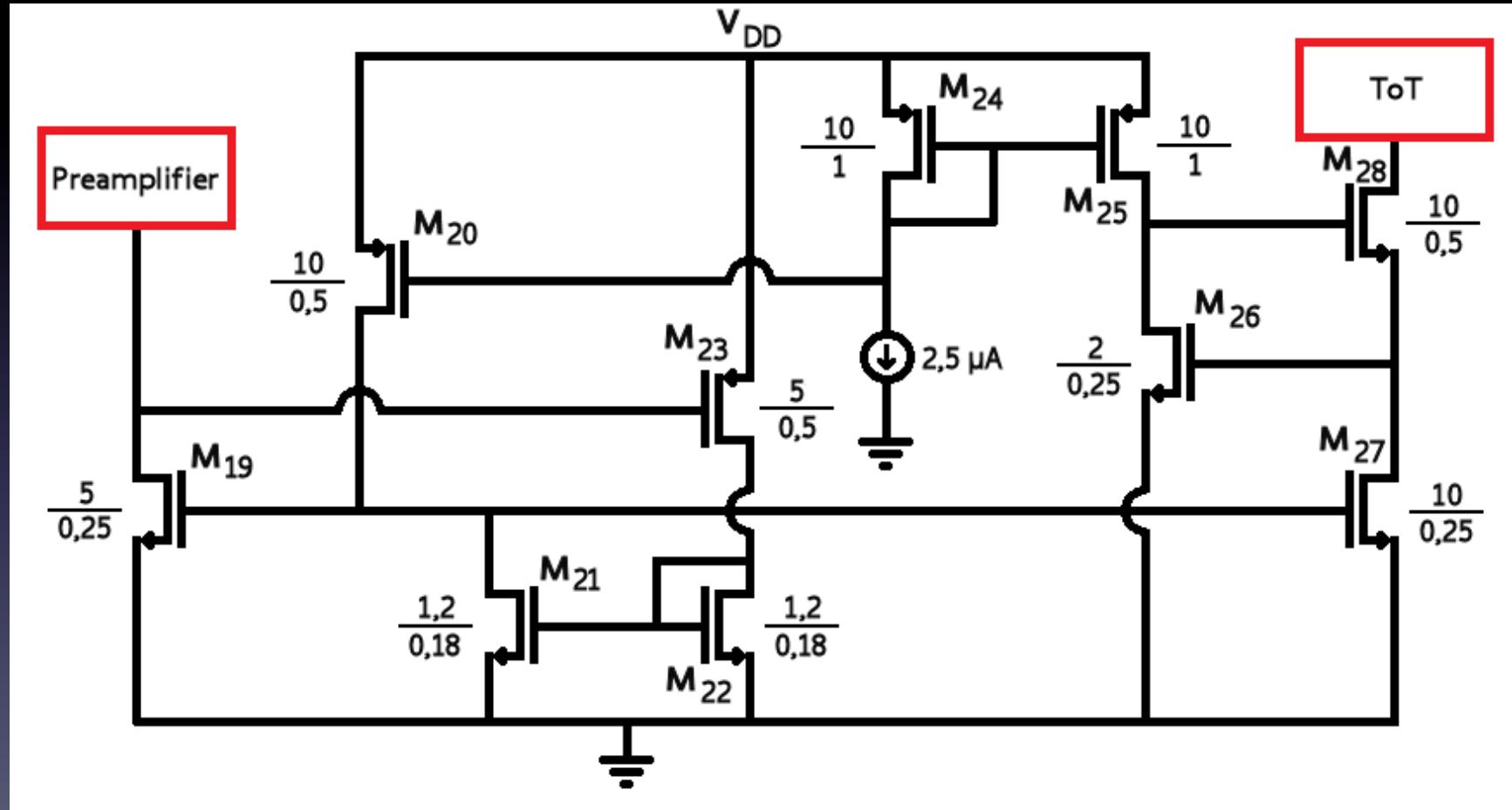
Current Buffer



Current Buffer with g_m -boosting

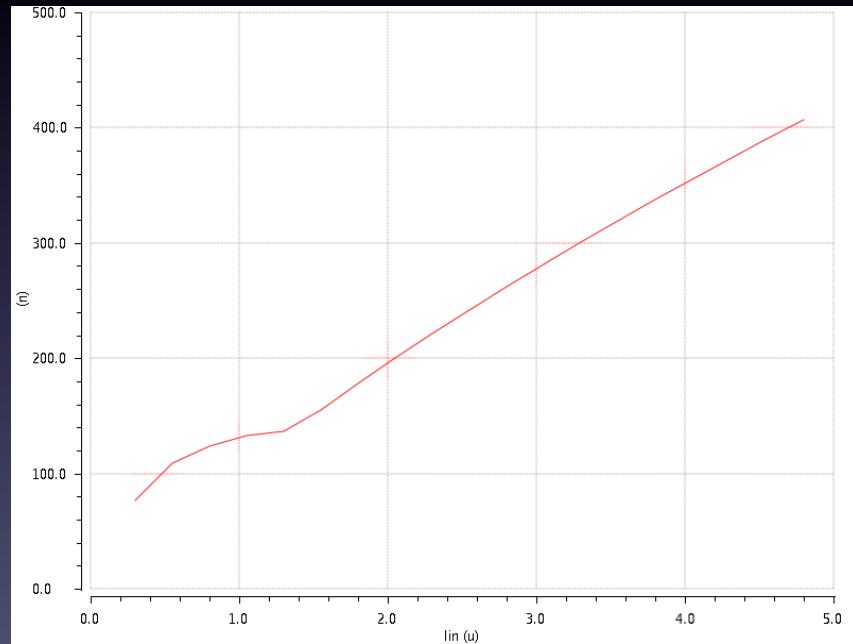


Implemented FE stage: Current Buffer (1)

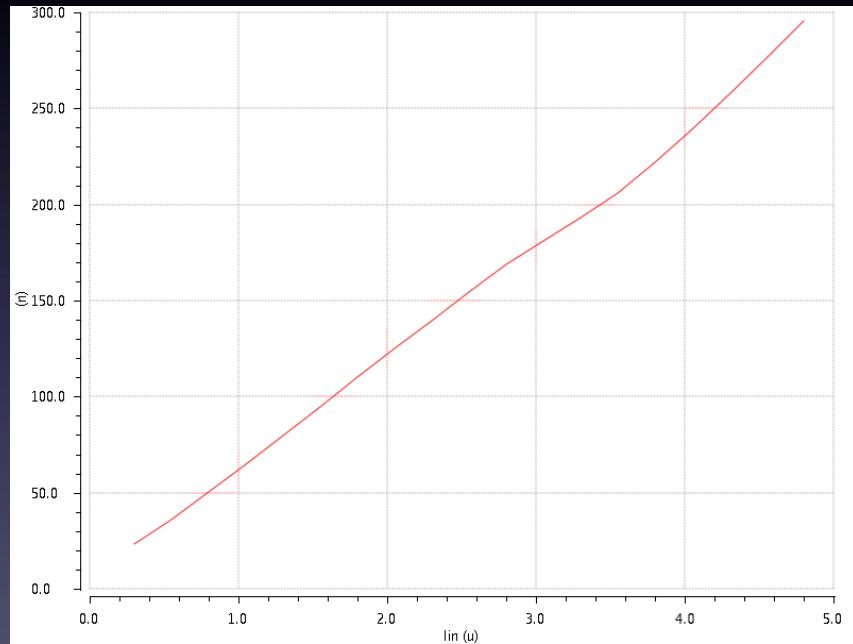


Implemented FE stage: Current Buffer (2)

Without g_m -boosting

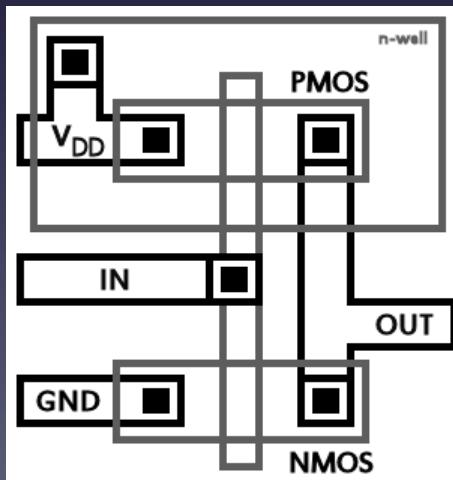
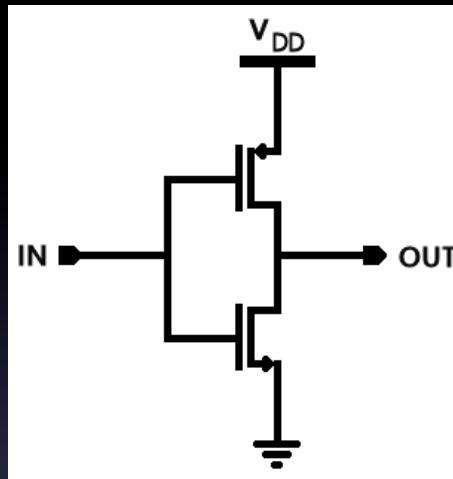


With g_m -boosting

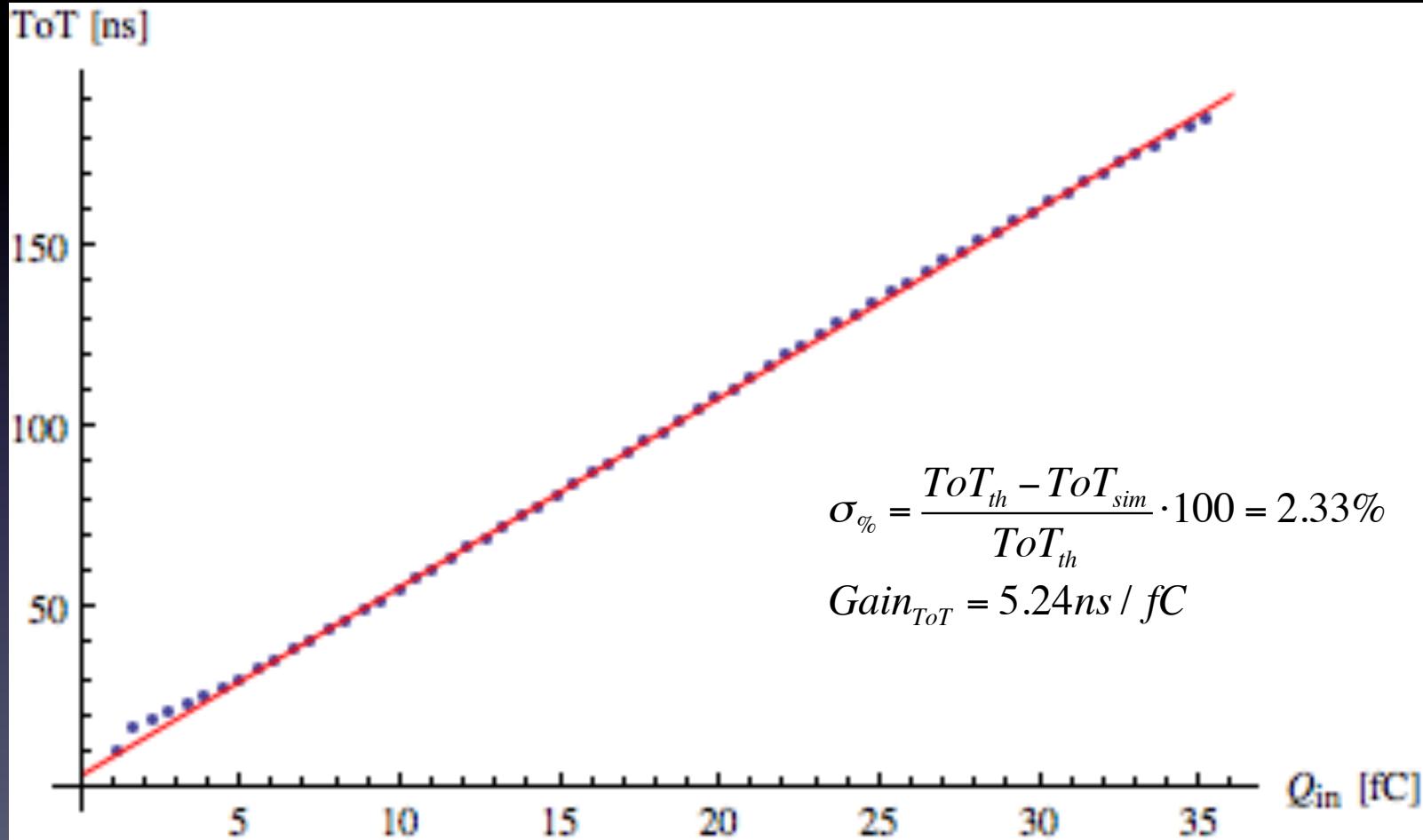


IC implementation flow

- Schematic design
- Layout design
- Post-layout verification
 - Simulations with passives
 - LVS (Layout VS Schematic)
- Manufacturing (~ 3 months)
- Typical manpower involved
 - ~ 10 years man

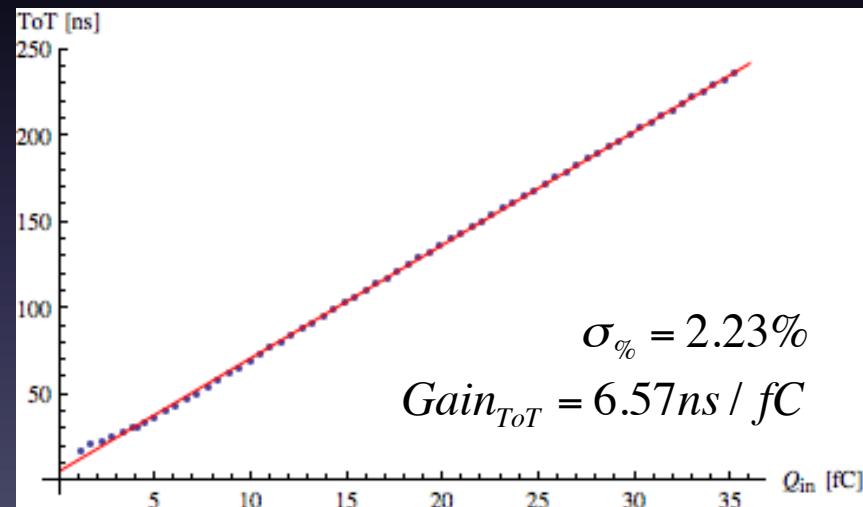


Simulations: Linearity

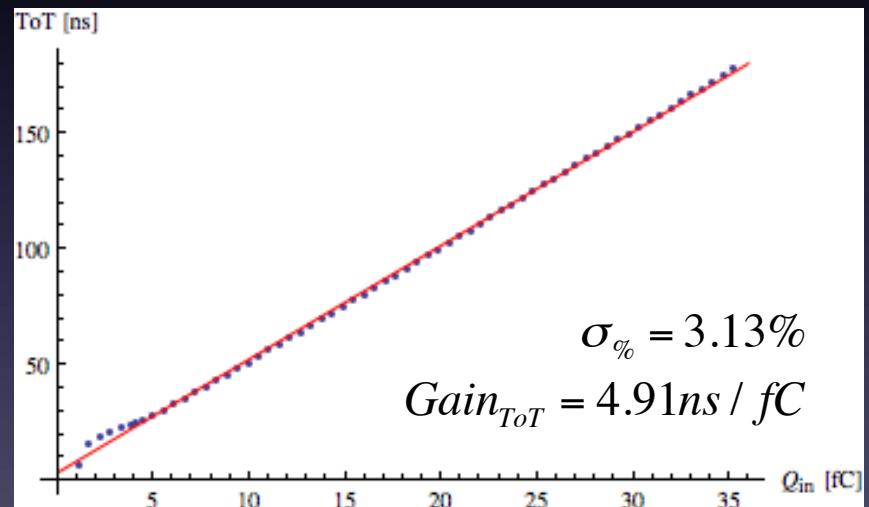


Simulations: Corner Process

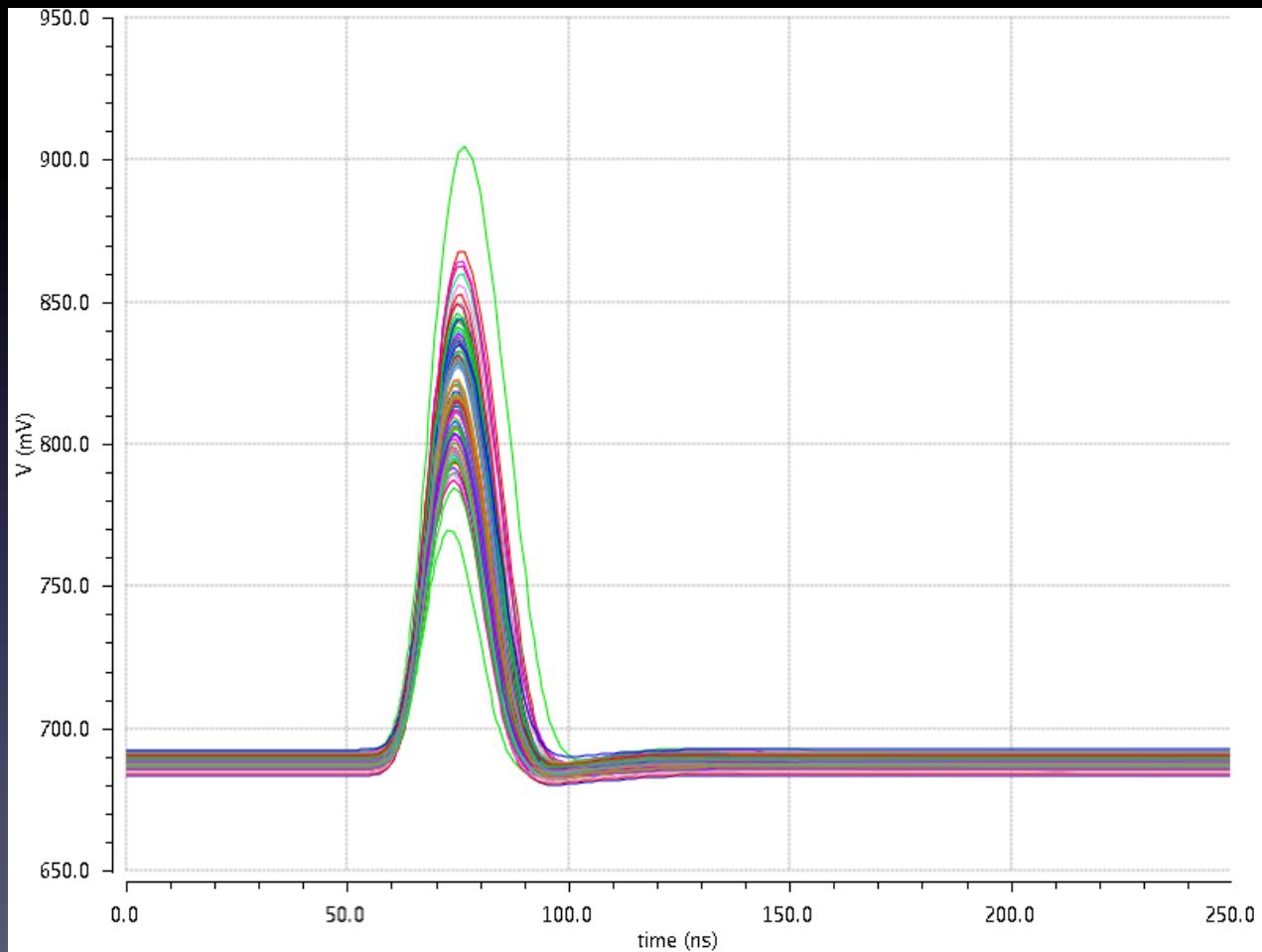
Slow-Slow configuration



Fast-Fast configuration

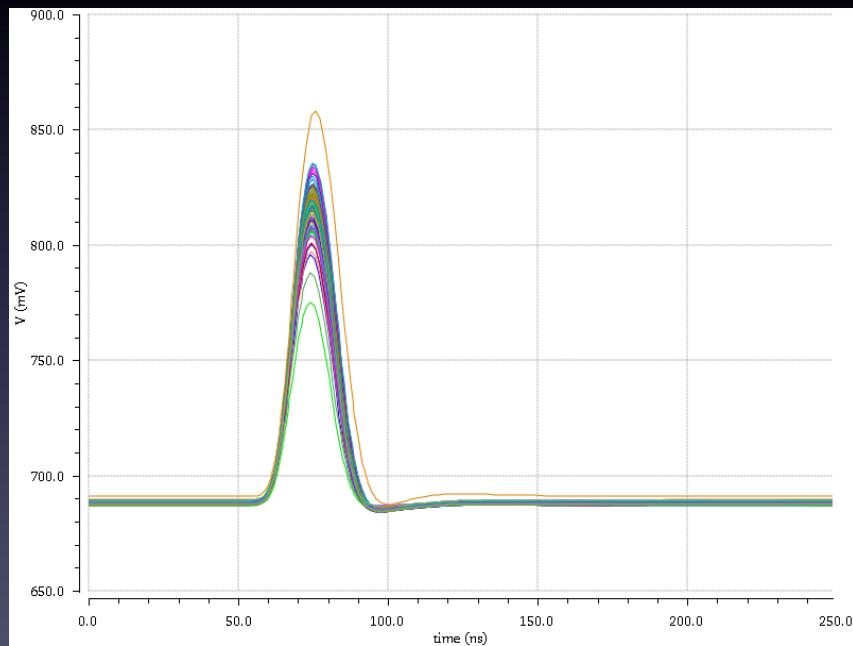


Simulations: Monte Carlo (1)

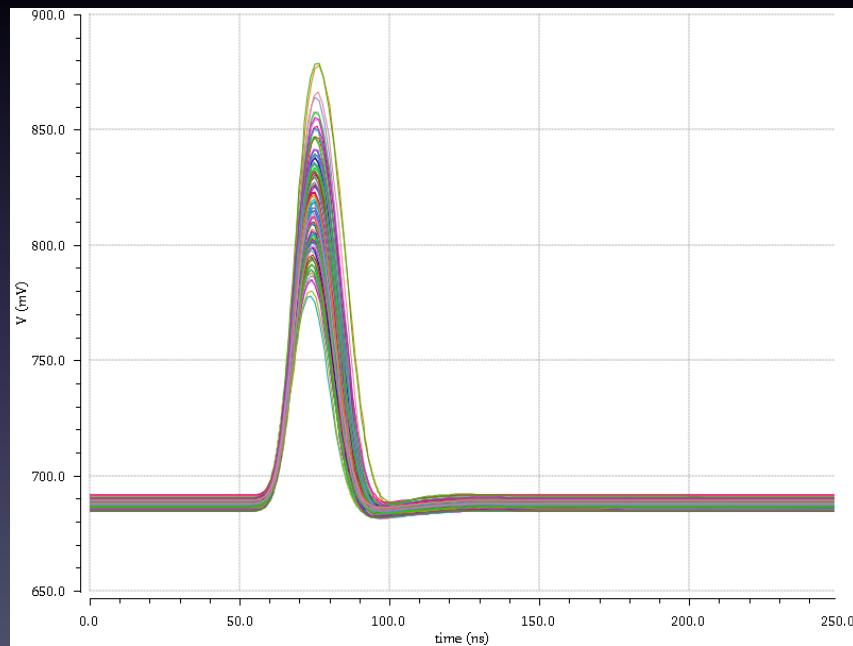


Simulations: Monte Carlo (2)

Process variations

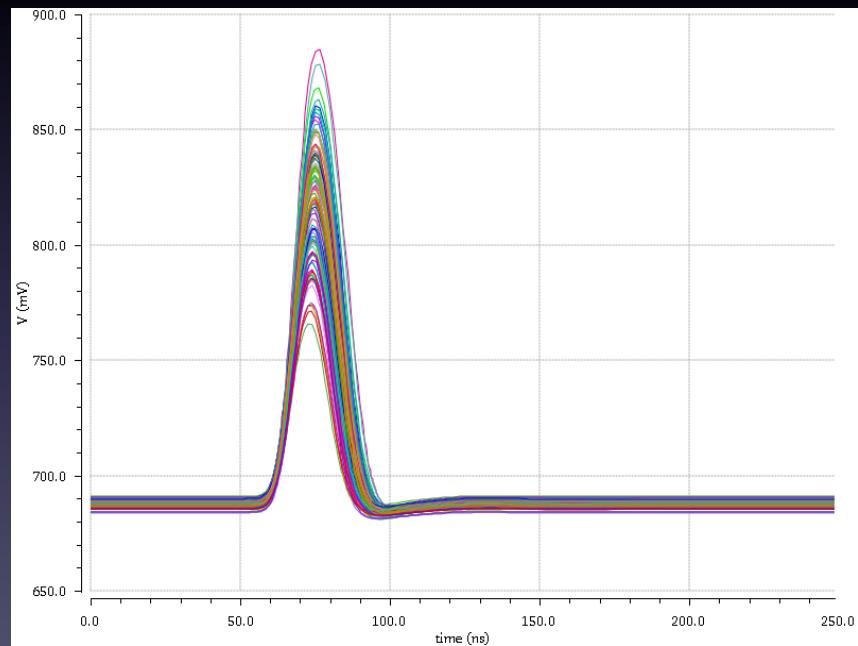


Mismatch variations

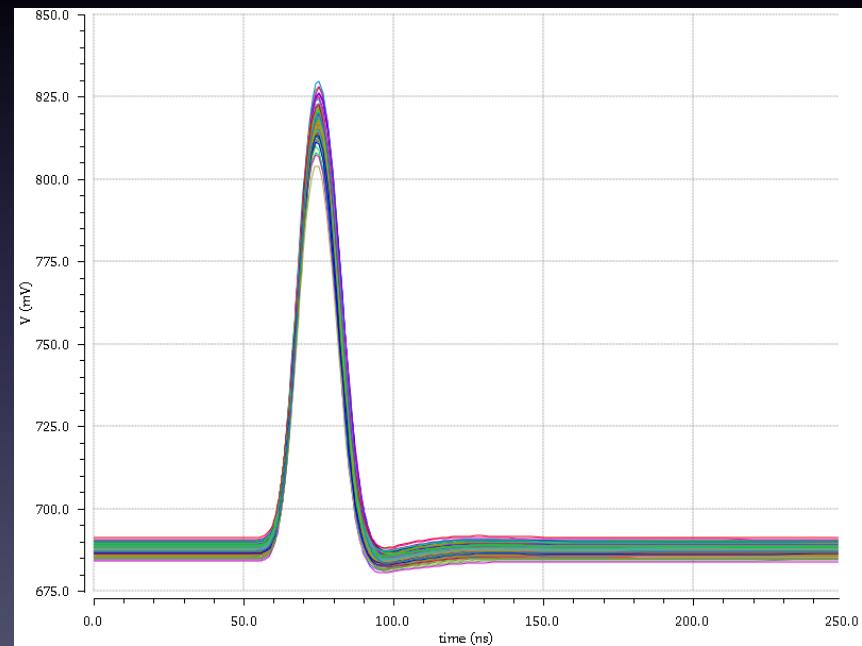


Simulations: Monte Carlo (3)

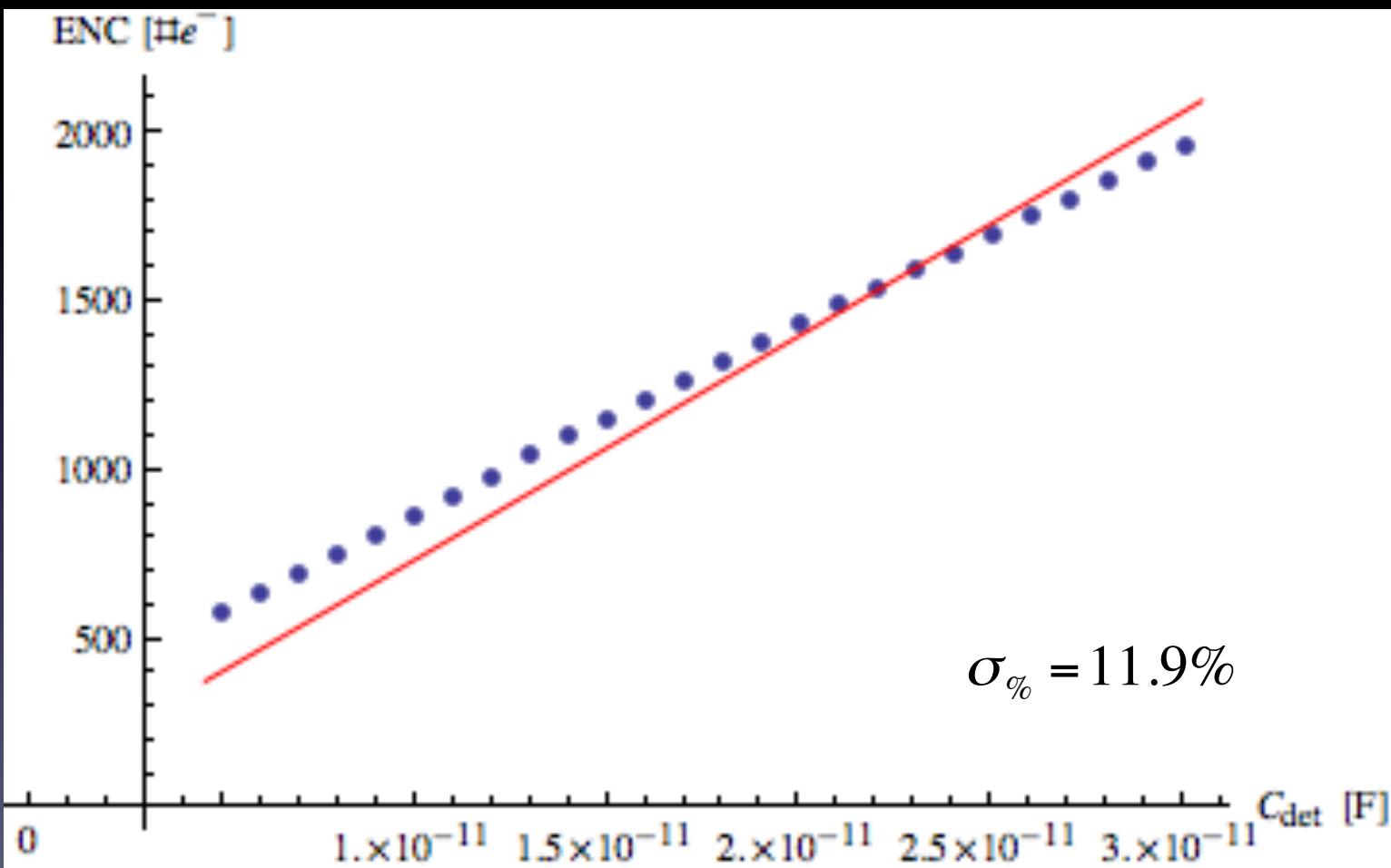
MC without input biasing current mirror



MC without current buffer current mirror



Simulations: Noise



Conclusions and perspectives

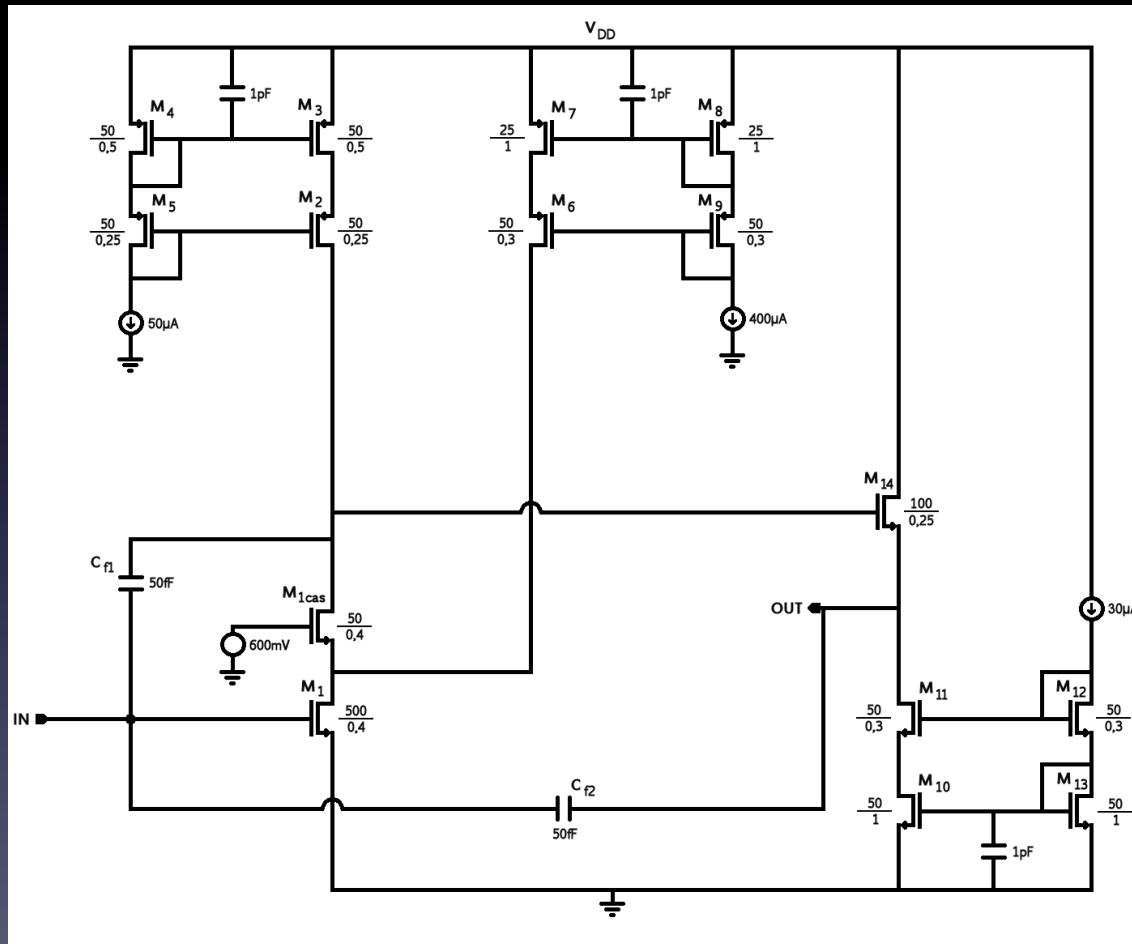
- Matching between electronics and physics simulations (performed by my German colleagues)
- Improvement of the ToT stage output linearity
- Topology adjustment to process signals of both polarities
- Layout design



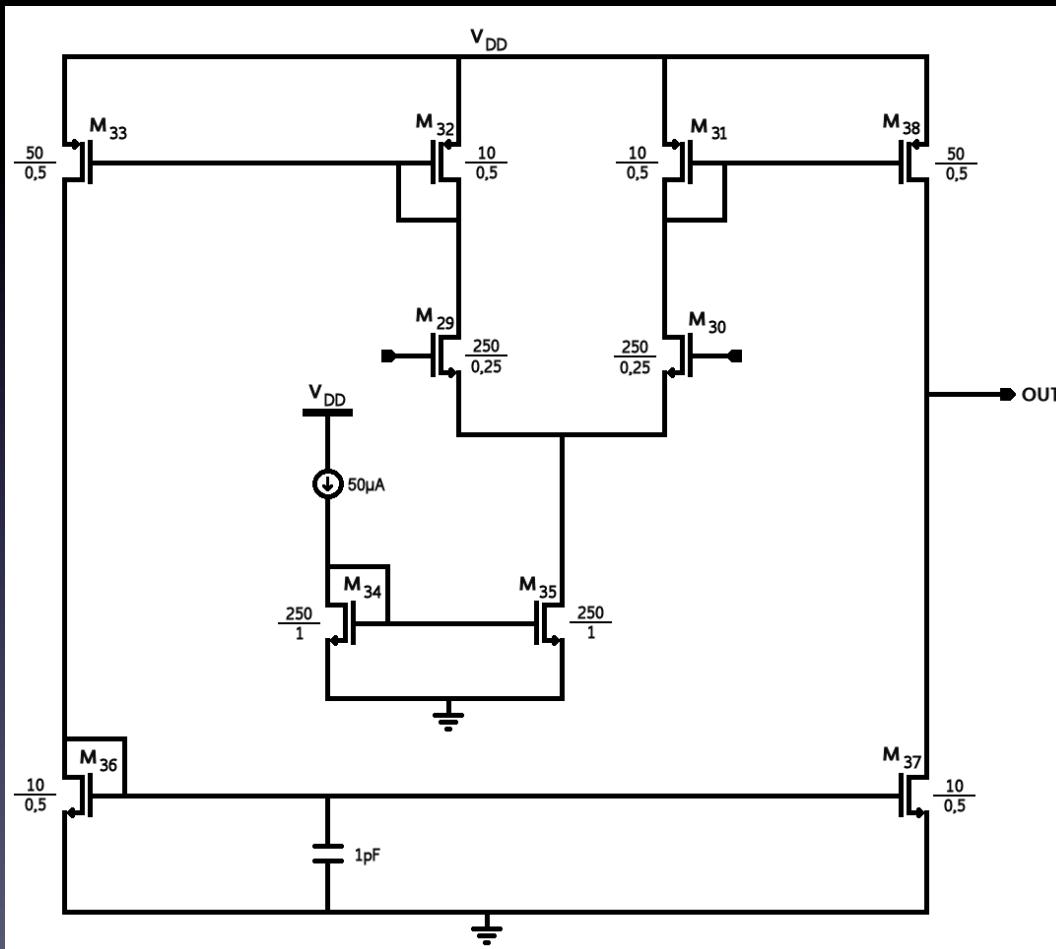
Thank you for your
kind attention

Backup Slides

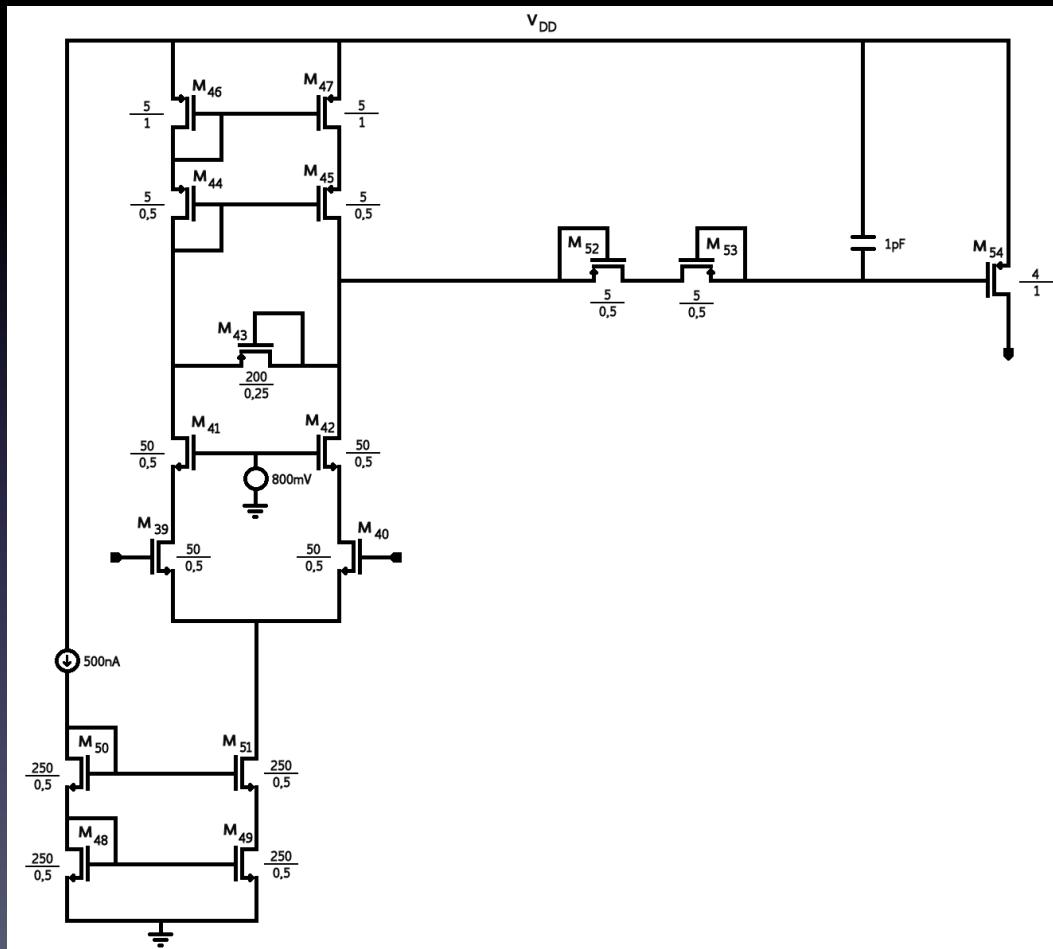
CSA schematic



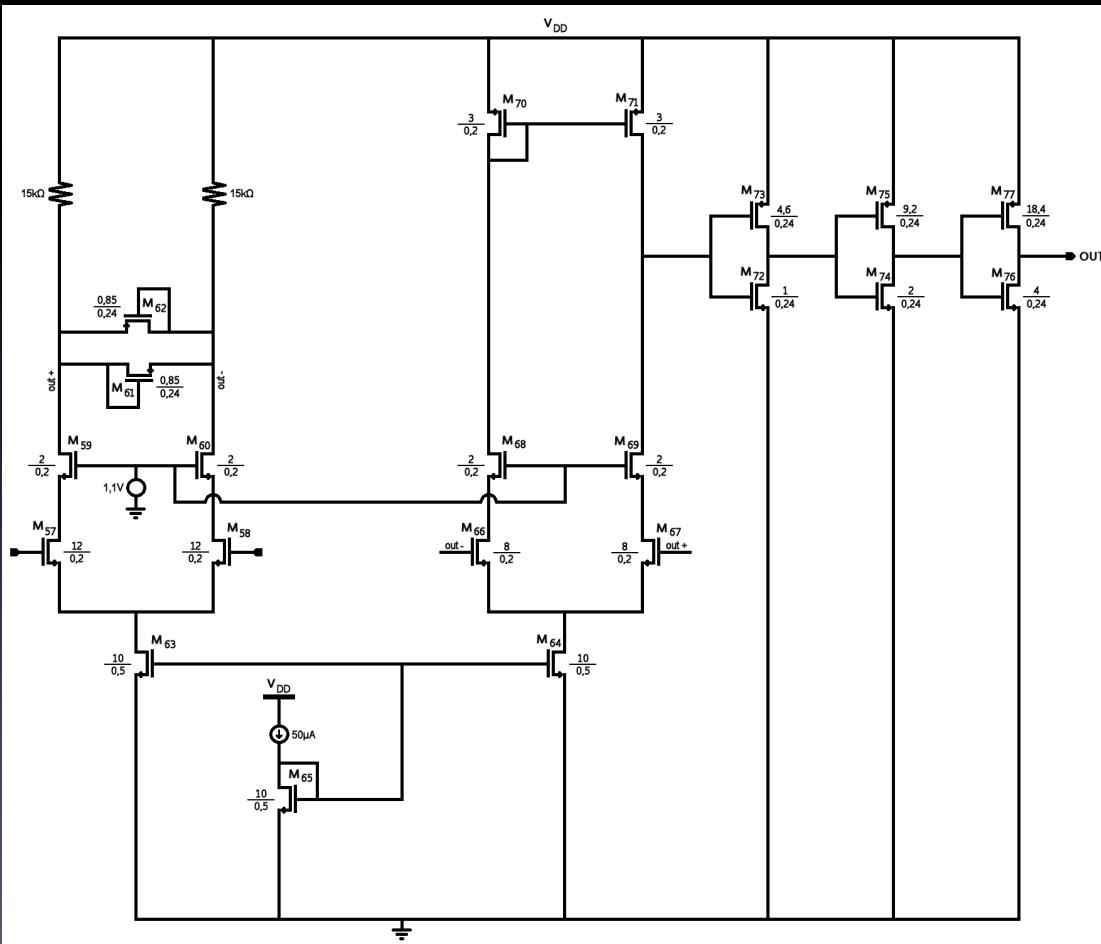
ToT Amplifier schematic



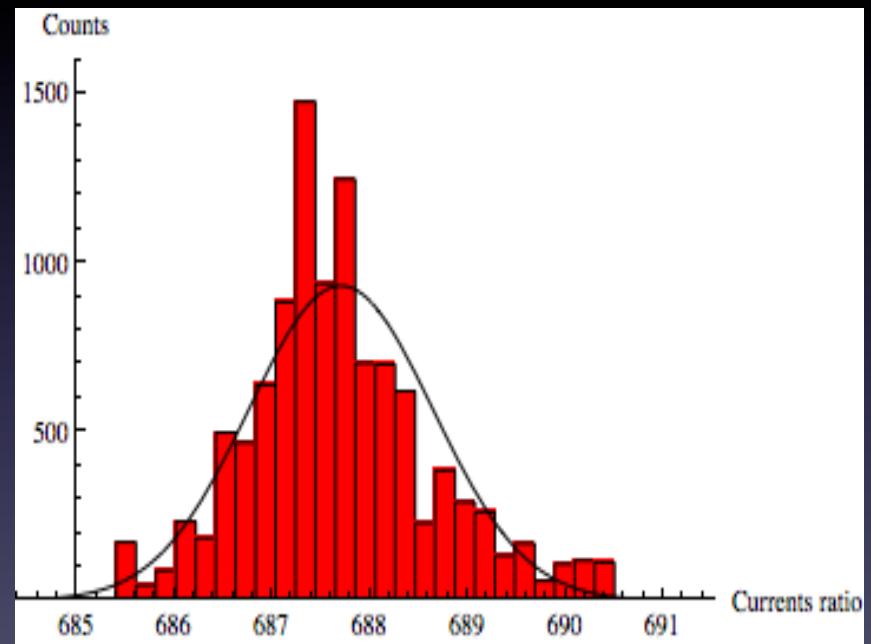
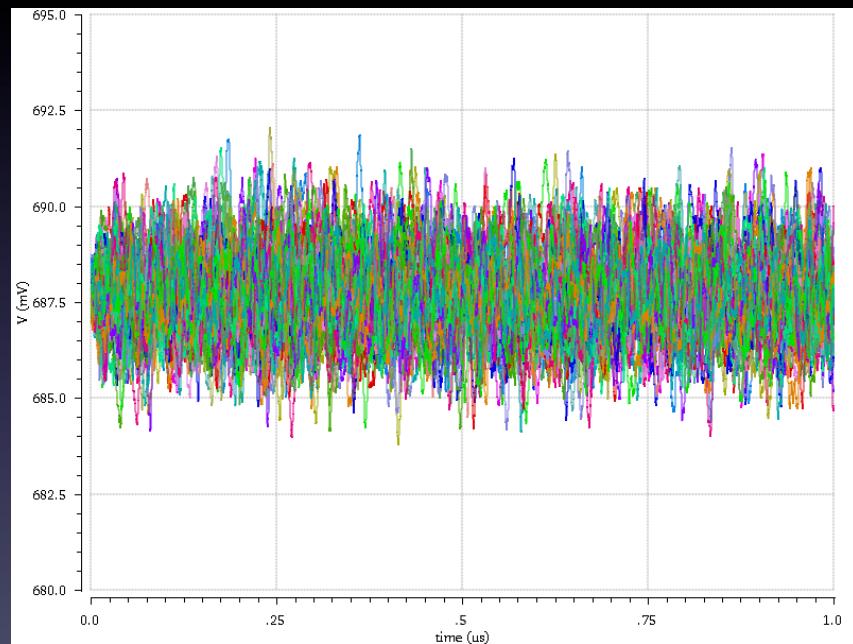
Baseline Holder schematic



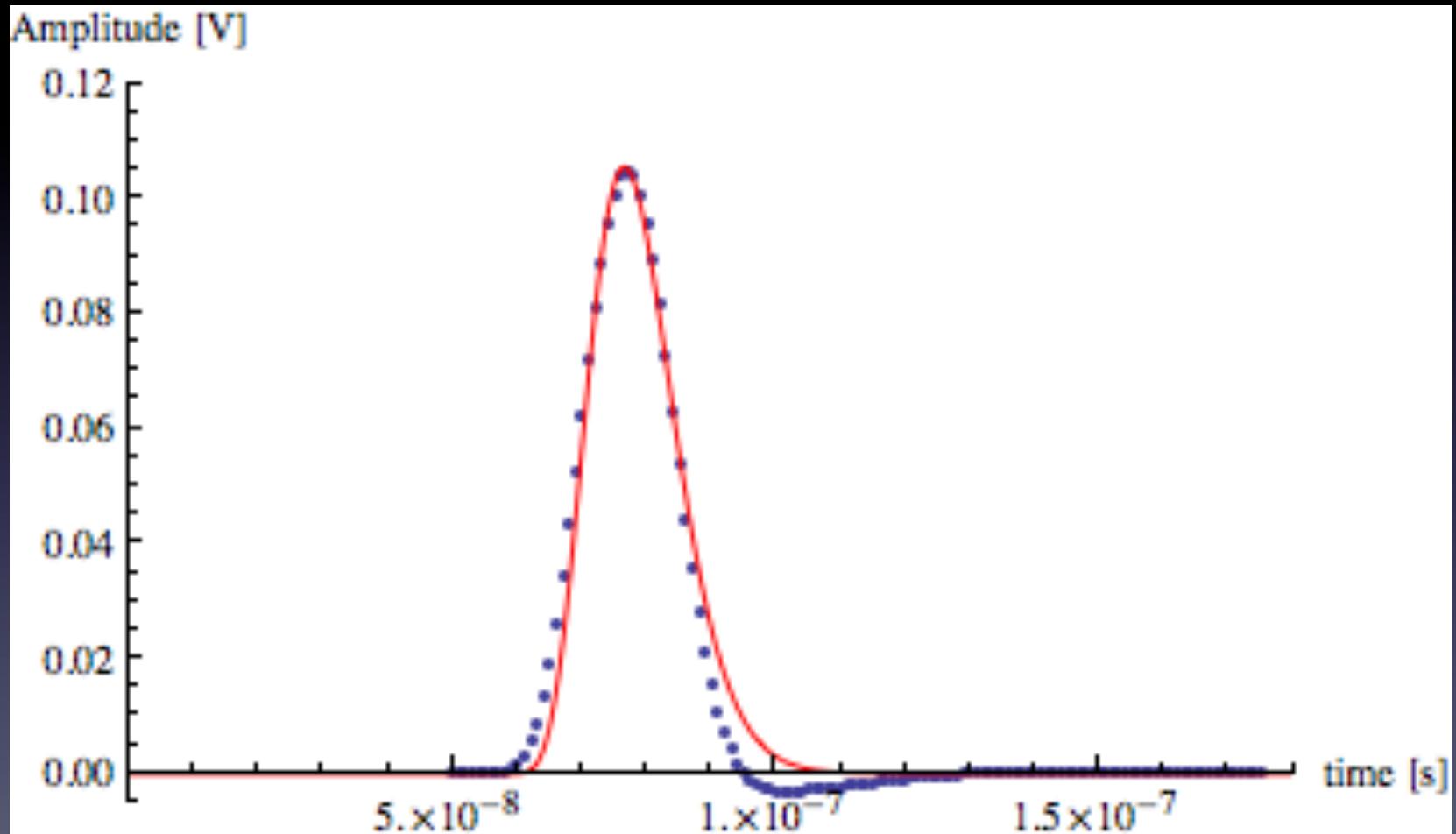
Comparator schematic



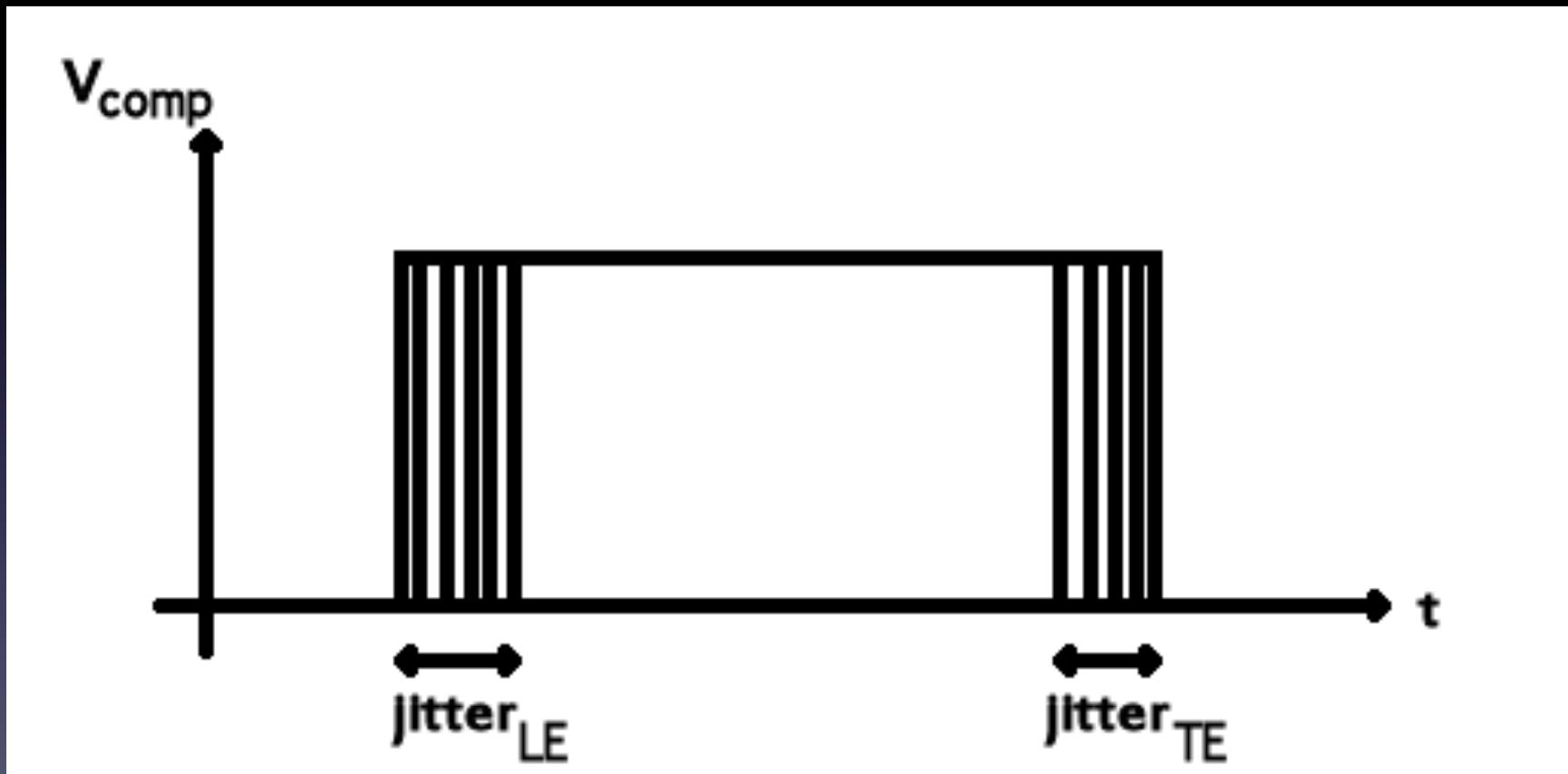
Simulations: Gaussian noise (1)



Simulations: Gaussian noise (2)

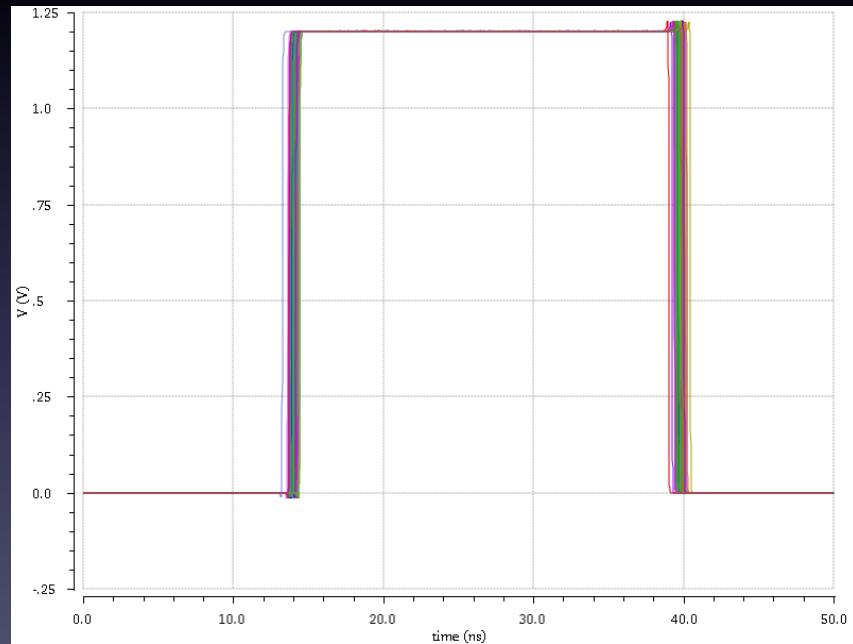


Simulations: Jitter (1)



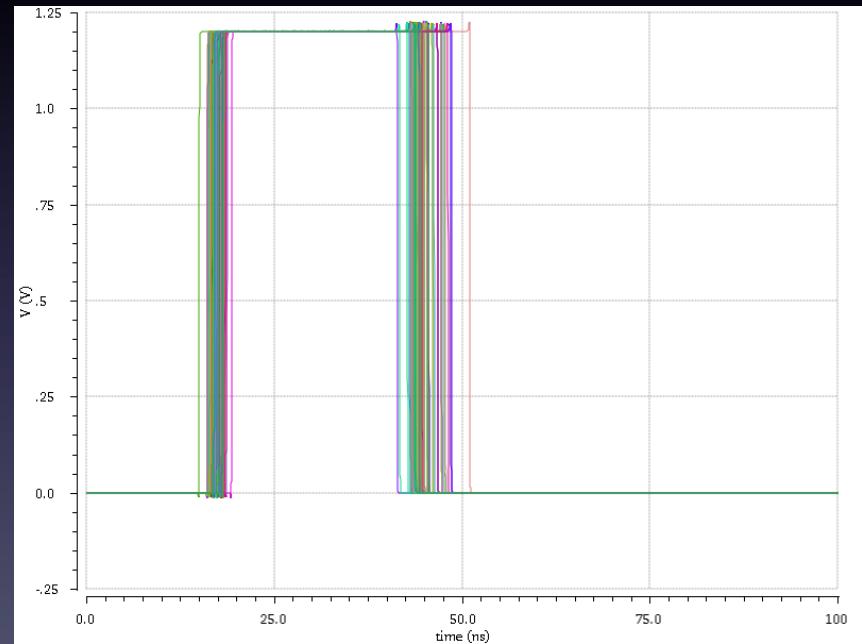
Simulations: Jitter (2)

$C_{\text{det}} = 5 \text{ pF}$



$\sigma_t \sim 300 \text{ ps}$

$C_{\text{det}} = 30 \text{ pF}$



$\sigma_t \sim 1.5 \text{ ns}$